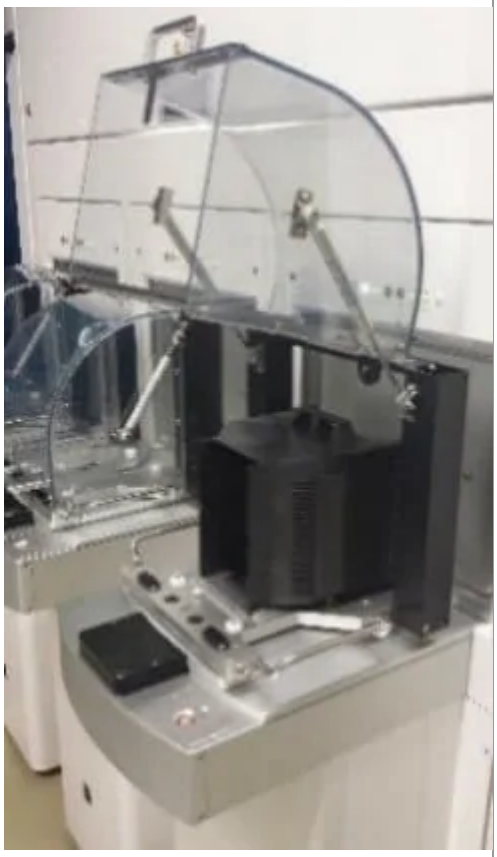
Helios® C200



The Helios C200 features an advanced temperature measurement and control system combined with an active compensation algorithm for different wafer emissivities. The Helios C200 RTP system combines superior technical performance with outstanding tool reliability. It is the ideal RTP solution for 200 mm semiconductor development and manufacturing.

Product Features and Advantages:

- **Unique Wafer Stress Management Capabilities**
  - Wafer double-side heating for best wafer stress management
  - RTP process for different substrate thickness
- **Superior Solution for Pattern-Loading Effect**
  - Wafer double-side heating coupled with proven DTEC control technology
  - Elimination of wafer-loading effect in RTP processes
- **Wide RTP Applications**
  - 200°C – 1300°C temperature range, from ultra-low temperature NiSi anneal to ultra-high temperature wafer engineering
  - Best metal contamination performance for CMOS sensor fabrication
  - Excellent ambient control capability, O_2 < 1 ppm
  - High power incandescent lamp, long lifetime
- **High Productivity System Platform**
  - Two process chambers
  - High speed wafer transfer
  - Small footprint
  - More than 300 platforms installed worldwide



Product Applications:

- **Power IC, CMOS Sensor, MEMS, Logic, LED**
  - Post implant ion activation
  - Ultra-shallow-junction formation
  - Metal silicide formation
  - High temperature anneal
- **Wafer Manufacturing**
  - High temperature wafer substrate anneal